

AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph [0111] with the following amended paragraph:

FIG. 29 is a view chart showing the chromaticity coordinate of the light-emitting device of Example 28 related to the present invention;

Please replace paragraph [0210] with the following amended paragraph:

In the light-emitting device of Embodiment 2, a light-emitting element 10 is composed of a sapphire substrate 1, a semiconductor layer 2 formed on the sapphire substrate 1, and positive and negative electrodes 3, 4 formed on the semiconductor layer 2. The light-emitting element 10 is die-bonded in the cup of the lead frame 13a, and the positive and negative electrodes are respectively connected with the lead frame 13a and the lead frame 13b by the electro-conductive wire 14. Further, the coating member 12 containing the phosphor 11 is formed in the cup of the lead frame 13a so as to cover the light-emitting element 10. Further, the mold member 15 is formed so as to cover the whole of the lead frame 13a and the lead frame 13b in which the coating member containing the light-emitting element and the phosphor 11 was provided.

Please replace paragraph [0211] with the following amended paragraph:

In the light-emitting device of Embodiment 2, the semiconductor layer 2 of the light-emitting element 10 comprises a plural number of layers including a luminescent layer (not illustrated), and the composition of the luminescent layer is adjusted so that

the luminescence peak wavelength becomes 500 nm or less at an ultraviolet to blue region. Further, the positive and negative electrodes 3,4 are 3 are formed on the same plane side of said semiconductor layer 2.

Please replace paragraph [0413] with the following amended paragraph:

Hereat, then-electrode 211a is an ohmic electrode which was brought in ohmic contact with the exposed face 203a of the n-type layer 203. After forming the p-side electrode 210 and the n-side electrode 211a for ohmic, the respective electrodes are brought in ohmic contact by being annealed by heat treatment. The p-side ohmic electrode (not shown) which was obtained at this time becomes an opaque film which hardly transmit the luminescence of the active layer 204.

Please replace paragraph [0424] with the following amended paragraph:

FIG. 30 is a view chart showing the cap type light-emitting device of Example 30 related to the present invention.